

## Final Product/Process Change Notification Document #: FPCN22134XD

Issue 1 February 2019

Title of Change:	Hydrazine elimination in ON Semiconductor Niigata Co., Ltd., Japan (OSNC).		
Proposed first ship date:	8 May 2019		
Contact information:	Contact your local ON Semiconductor Sales Office or < <u>Yukio.Kudo@onsemi.com</u> >		
Samples:	Contact your local ON Semiconductor Sales Office or < <a href="mailto:PCN.samples@onsemi.com">PCN.samples@onsemi.com</a> Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or < Satoru.Fujinuma@onsemi.com >.		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sentto customers. FPCNs are issued 90 days prior to implementation of the change.  ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact < PCN.Support@onsemi.com>		
Change Part Identification:	Date Code		
Change Category:	✓ Wafer Fab Change		
Change Sub-Category(s):  Manufacturing Site Add Manufacturing Site Tran Manufacturing Process	sfer Product specific change	☐ Datasheet/Product Doc change ☐ Shipping/Packaging/Marking ☐ Other:	
Sites Affected:	ON Semiconductor Sites: ON Niigata, Japan	External Foundry/Subcon Sites: None	
	es the elimination of Hydrazine in ON Semiconductor Ni rohibited chemical in ON Semiconductor as it is consider	• , ,	

The related products are transferred to a process that does not use Hydrazine on the same site ON Semiconductor Niigata, Japan (OSNC).

Change Point	Before Change Description	After Change Description
Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=10)	N1 Fab (Minimum rule=0.8um, Class=10) AND N2 Fab (Minimum rule=0.25um, Class=1)
Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)
Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide

TEM001793 Rev. A Page 1 of 2



# Final Product/Process Change Notification Document #: FPCN22134XD

Issue 1 February 2019

#### **Reliability Data Summary:**

**QV DEVICE NAME: LB11870-TRM-E** PACKAGE: HSSOP48(375mil)

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

#### **Electrical Characteristic Summary:**

There is no change in the electrical performance. Datasheet specifications remain unchanged.

#### **List of Affected Parts:**

Note: Only the standard (offthe shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the PCN Customized Portal.

Part Number	Qualification Vehicle	
LA6581DMR2G		
LB11961-TLM-H		
LB11961-TLM-E	LB11870-TRM-E	
LB11970FV-TLM-H		
LA6583MC-AH		
LB11685AV-TLM-H		

TEM001793 Rev. A Page 2 of 2

ON	Semiconductor®	ON
----	----------------	----

### **Appendix A: Changed Products**

D

Product	Customer Part Number	Qualification Vehicle
LA6581DMR2G		LB11870-TRM-E
LA6583MC-AH		LB11870-TRM-E
LB11685AV-TLM-H		LB11870-TRM-E
LB11961-TLM-E		LB11870-TRM-E
LB11961-TLM-H		LB11870-TRM-E
I B11970FV-TI M-H	Î	I B11870-TRM-F